

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

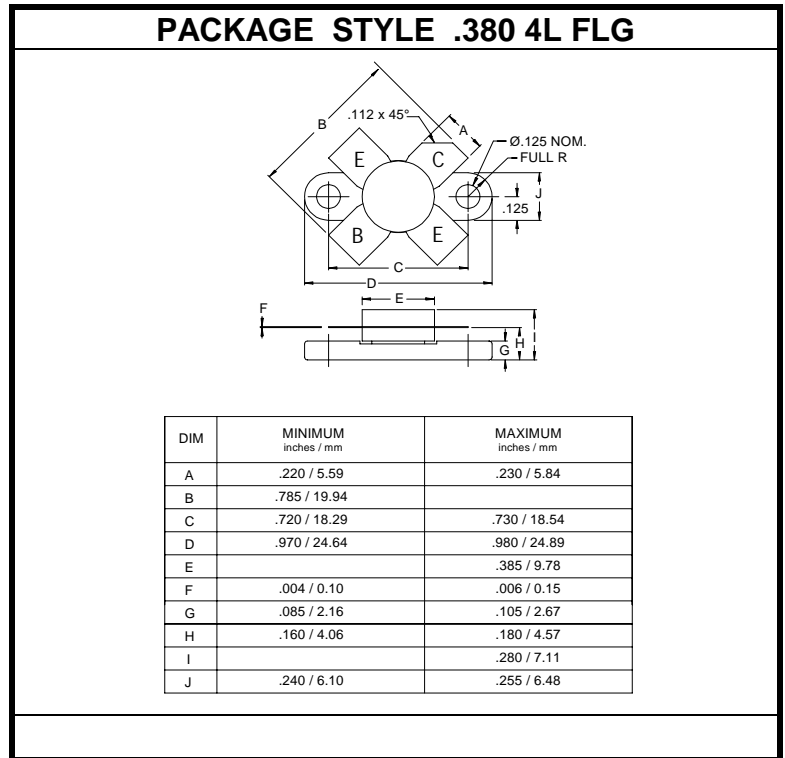
The **ASI BLY93C** is Designed for Class C, 28 V High Band Applications up to 175 MHz.

FEATURES:

- Common Emitter
- $P_G = 9.0$ dB at 25 W/175 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	3.0 A
V_{CBO}	65 V
V_{CEO}	35 V
V_{EBO}	4.0 V
P_{DISS}	70 W @ $T_C = 25^\circ\text{C}$
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	2.5 °C/W


CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 50$ mA	35			V
BV_{CES}	$I_C = 10$ mA	65			V
BV_{EBO}	$I_E = 10$ mA	4.0			V
I_{CES}	$V_{CE} = 36$ V			4.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 1.25$ A	10		100	---
C_{OB}	$V_{CB} = 28$ V $f = 1.0$ MHz		45		pF
G_P	$V_{CE} = 28$ V $f = 175$ MHz	9.0			dB
f_T	$V_{CB} = 28$ V $I_E = 200$ mA $f = 100$ MHz		625		MHZ